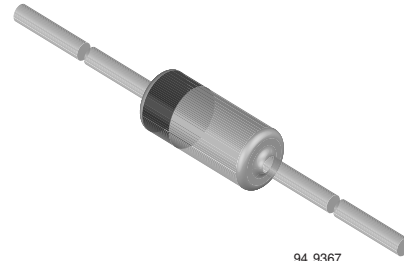


Small Signal Zener Diodes

Features

- Zener voltage specified at 50 μA
- Maximum delta V_Z given from 10 μA to 100 μA
- Very high stability
- Low noise
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



94 9367

Applications

Voltage stabilization

Mechanical Data

Case: DO-35 Glass case

Weight: approx. 125 mg

Packaging codes/options:

TR / 10 k per 13 " reel, 30 k/box

TAP / 10 k per Ammo tape (52 mm tape), 30 k/box

Absolute Maximum Ratings

$T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Power dissipation	$I = 4\text{ mm}$	P_{tot}	500	mW
Z-current		I_Z	P_{tot}/V_Z	mA

Thermal Characteristics

$T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction temperature		T_j	175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^{\circ}\text{C}$
Junction ambient	$I = 4\text{ mm}$, $T_L = \text{constant}$	R_{thJA}	300	K/W

Electrical Characteristics

$T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100\text{ mA}$	V_F			1.5	V

Electrical Characteristics

Partnumber ¹⁾	Zener Voltage			Max.Reverse Current	Test Voltage	Max. Zener Current	Max. Voltage Change
	$V_Z @ I_Z = 50 \mu A$			I_R ³⁾	V_R ³⁾	I_{ZM} ²⁾	ΔV_Z ⁴⁾
	typ. ¹⁾	min.	max	μA	V	mA	V
1N4678	1.8	1.71	1.89	7.5	1	120	0.70
1N4679	2	1.9	2.1	5	1	110	0.70
1N4680	2.2	2.09	2.31	4	1	100	0.75
1N4681	2.4	2.28	2.52	2	1	95	0.80
1N4682	2.7	2.565	2.835	1	1	90	0.85
1N4683	3	2.85	3.15	0.8	1	85	0.90
1N4684	3.3	3.135	3.465	7.5	1.5	80	0.95
1N4685	3.6	3.42	3.78	7.5	2	75	0.95
1N4686	3.9	3.705	4.095	5	2	70	0.97
1N4687	4.3	4.085	4.515	4	2	65	0.99
1N4688	4.7	4.465	4.935	10	3	60	0.99
1N4689	5.1	4.845	5.355	10	3	55	0.97
1N4690	5.6	5.32	5.88	10	4	50	0.96
1N4691	6.2	5.89	6.51	10	5	45	0.95
1N4692	6.8	6.46	7.14	10	5.1	35	0.90
1N4693	7.5	7.125	7.875	10	5.7	31.8	0.75
1N4694	8.2	7.79	8.61	1	6.2	29	0.5
1N4695	8.7	8.265	9.135	1	6.6	27.4	0.1
1N4696	9.1	8.645	9.555	1	6.9	26.2	0.08
1N4697	10	9.5	10.5	1	7.6	24.8	0.1
1N4698	11	10.45	11.55	0.05	8.4	21.6	0.11
1N4699	12	11.4	12.6	0.05	9.1	20.4	0.12
1N4700	13	12.35	13.65	0.05	9.8	19	0.13
1N4701	14	13.3	14.7	0.05	10.6	17.5	0.14
1N4702	15	14.25	15.75	0.05	11.4	16.3	0.15
1N4703	16	15.2	16.8	0.05	12.1	15.4	0.16
1N4704	17	16.15	17.85	0.05	12.9	14.5	0.17
1N4705	18	17.1	18.9	0.05	13.6	13.2	0.18
1N4706	19	18.05	19.95	0.05	14.4	12.5	0.19
1N4707	20	19	21	0.01	15.2	11.9	0.2
1N4708	22	20.9	23.1	0.01	16.7	10.8	0.22
1N4709	24	22.8	25.2	0.01	18.2	9.9	0.24
1N4710	25	23.75	26.25	0.01	19	9.5	0.25
1N4711	27	25.65	28.35	0.01	20.4	8.8	0.27
1N4712	28	26.6	29.4	0.01	21.2	8.5	0.28
1N4713	30	28.5	31.5	0.01	22.8	7.9	0.3
1N4714	33	31.35	34.65	0.01	25	7.2	0.33
1N4715	36	34.2	37.8	0.01	27.3	6.6	0.36
1N4716	39	37.05	40.95	0.01	29.6	6.1	0.39
1N4717	43	40.85	45.15	0.01	32.6	5.5	0.43

¹⁾ Tolerancing and voltage designation (V_Z). The type numbers shown have a standard tolerance of $\pm 5\%$ on the nominal zener voltage.

²⁾ Maximum zener current ratings (I_{ZM}). Maximum zener current ratings are based on maximum zener voltage of the individual units.

³⁾ Reverse leakage current (I_R). Reverse leakage currents are guaranteed and measured at V_R as shown on the table.

⁴⁾ Maximum voltage change (ΔV_Z). Voltage change is equal to the difference between V_Z at $100 \mu A$ and V_Z at $10 \mu A$.

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

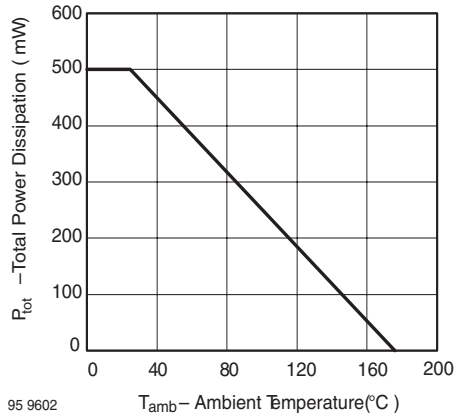


Figure 1. Total Power Dissipation vs. Ambient Temperature

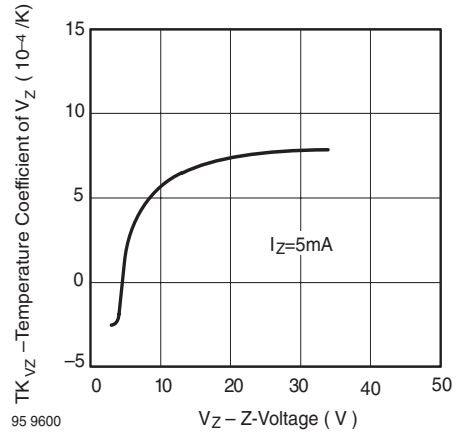


Figure 4. Temperature Coefficient of V_Z vs. Z-Voltage

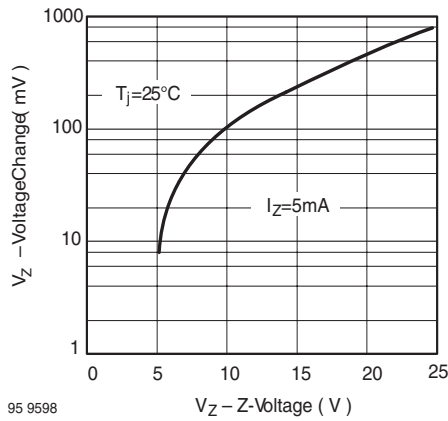


Figure 2. Typical Change of Working Voltage under Operating Conditions at $T_{amb}=25\text{ }^{\circ}\text{C}$

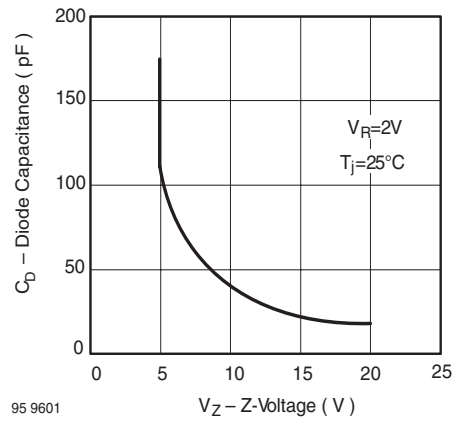


Figure 5. Diode Capacitance vs. Z-Voltage

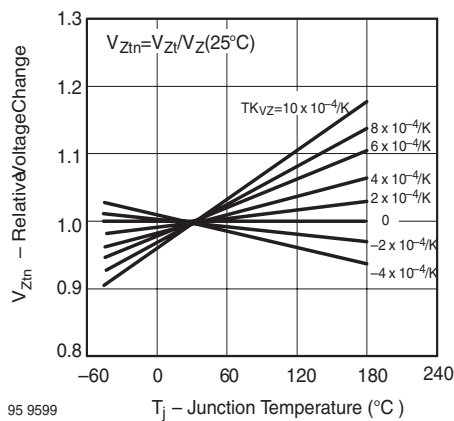


Figure 3. Typical Change of Working Voltage vs. Junction Temperature

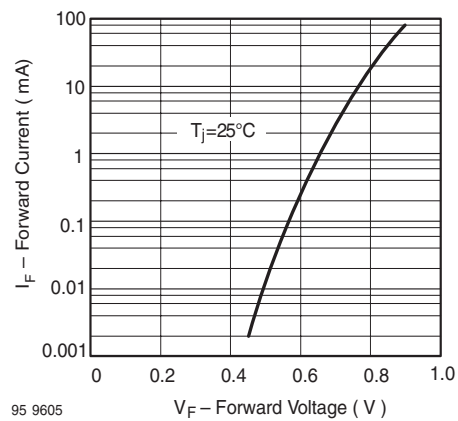


Figure 6. Forward Current vs. Forward Voltage

1N4678 to 1N4717

Vishay Semiconductors

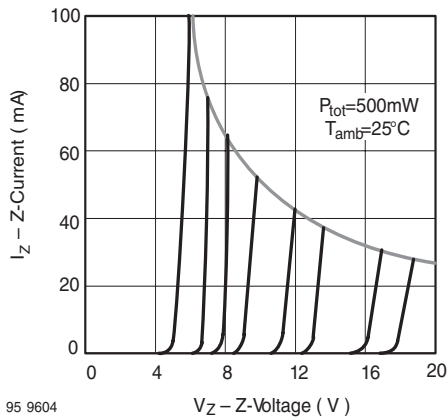


Figure 7. Z-Current vs. Z-Voltage

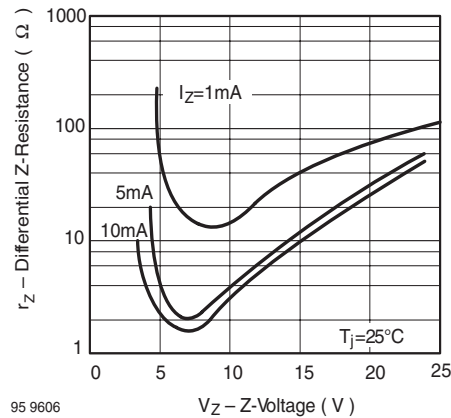


Figure 9. Differential Z-Resistance vs. Z-Voltage

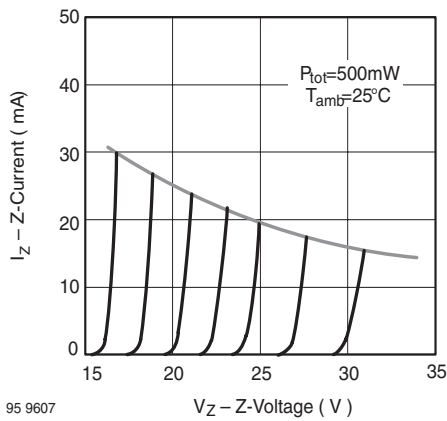


Figure 8. Z-Current vs. Z-Voltage

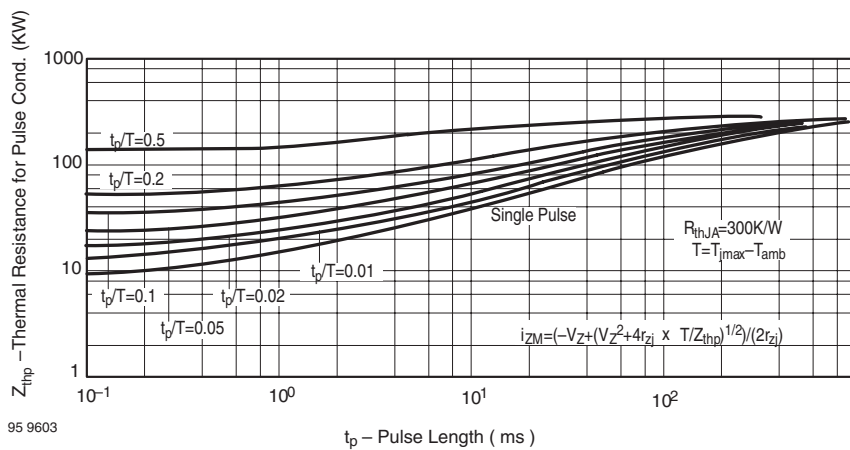
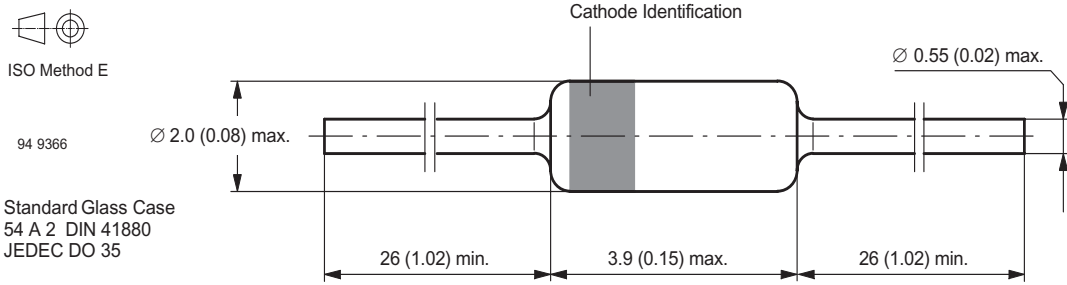


Figure 10. Thermal Response

Package Dimensions in mm (Inches)



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.